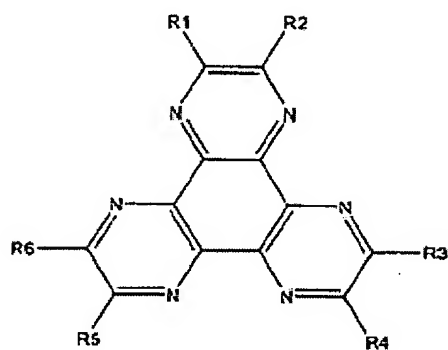


What is claimed is:

1. An organic transistor, comprising:

an organic layer inserted between a semi-conducting layer and a source or drain electrode,

wherein the organic layer includes at least one compound represented by Chemical Formula I.



Formula I

2. The organic transistor of claim 1, wherein the organic layer is further inserted between the semi-conducting layer and the source and drain electrodes.

3. The organic transistor of claim 1, further comprising:

a substrate;

a gate electrode disposed in the substrate;

an insulating layer disposed over the gate electrode and the substrate;

the semi-conducting layer disposed on the insulating layer; and

the source and drain electrodes disposed over the semi-conducting layer and the insulating layer.

4. The organic transistor of claim 1, further comprising:

a substrate;

a gate electrode disposed in the substrate;

an insulating layer disposed over the gate electrode and the substrate;

the source and drain electrodes disposed on the insulating layer; and

the semi-conducting layer disposed over the insulating layer and the source and drain electrodes.

5. The organic transistor of claim 1, further comprising:

a substrate;

the source and drain electrodes disposed on the substrate;

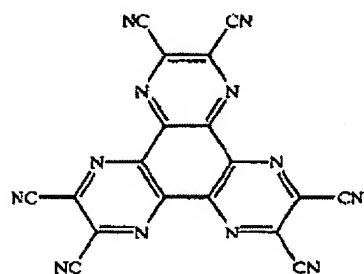
the semi-conducting layer disposed over the substrate and the source and drain electrodes;

an insulating layer disposed on the semi-conducting layer; and

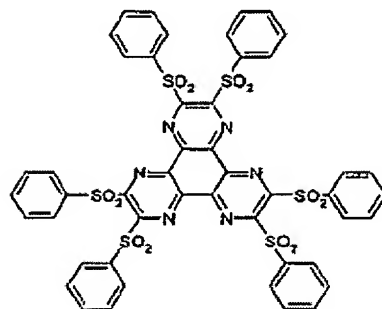
a gate electrode disposed in the insulating layer.

6. The organic transistor of claim 1, further comprising:
- a substrate;
 - the semi-conducting layer disposed in the substrate;
 - the source and drain electrodes disposed in the semi-conducting layer;
 - an insulating layer disposed on the semi-conducting layer and the source and drain electrodes; and
 - a gate electrode disposed in the insulating layer.
7. The organic transistor of claim 1, wherein the source or drain electrode include aluminum, silver, gold, neodymium, palladium, platinum, gold, or alloys of the foregoing metals.
8. The organic transistor of claim 1, wherein the source or drain electrode include composite materials including aluminum or silver.

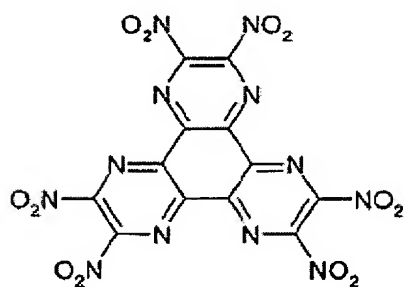
9. The organic transistor of claim 1, wherein the chemical compound I includes one of the following compounds Ia to Ig.



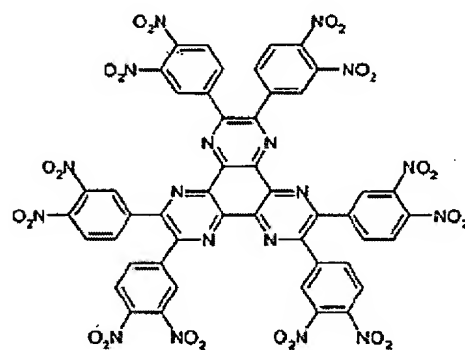
Formula Ia



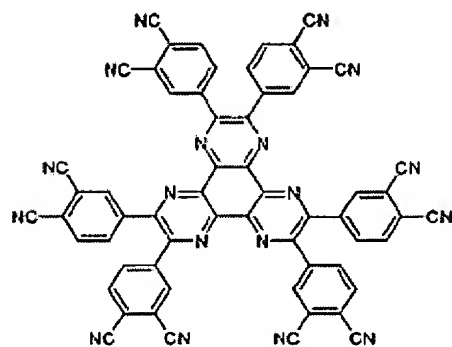
Formula Ib



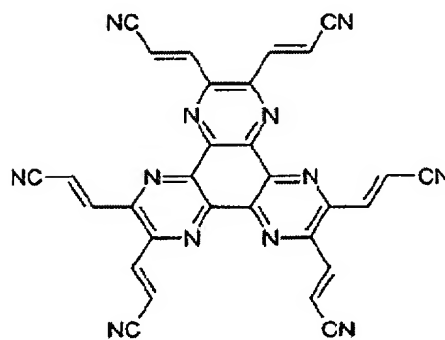
Formula Ic



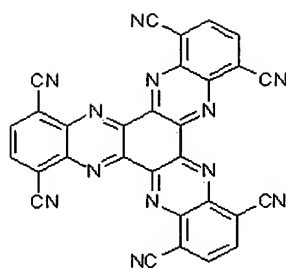
Formula Id



Formula Ie

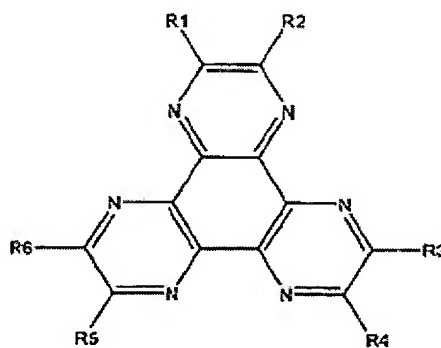


Formula If



Formula Ig

10. A method for manufacturing an organic transistor, comprising:
 inserting an organic layer between a semi-conducting layer and a source or drain electrode to improve electric contact between the semi-conducting layer and the source or drain electrode,
 wherein the organic layer includes at least one compound represented by Chemical Formula I.



Formula I

11. The method of claim 10, further comprising inserting the organic layer between the semi-conducting layer and the source and drain electrodes.

12. The method of claim 10, further comprising:

forming a gate electrode in a substrate;

forming an insulating layer over the gate electrode and the substrate;

forming the semi-conducting layer on the insulating layer; and

forming the source and drain electrodes over the semi-conducting layer and the insulating layer.

13. The method of claim 10, further comprising:

forming a gate electrode in a substrate;

forming an insulating layer over the gate electrode and the substrate;

forming the source and drain electrodes on the insulating layer; and

forming the semi-conducting layer over the insulating layer and the source and drain electrodes.

14. The method of claim 10, further comprising:

forming the source and drain electrodes on a substrate;

forming the semi-conducting layer over the substrate and the source and drain electrodes;

forming an insulating layer on the semi-conducting layer; and

forming a gate electrode in the insulating layer.

15. The method of claim 10, further comprising:

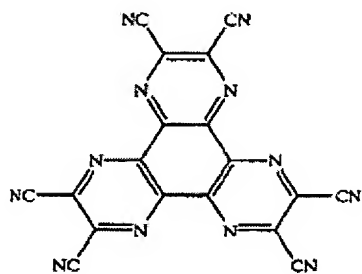
forming the semi-conducting layer in a substrate;

forming the source and drain electrodes in the semi-conducting layer;

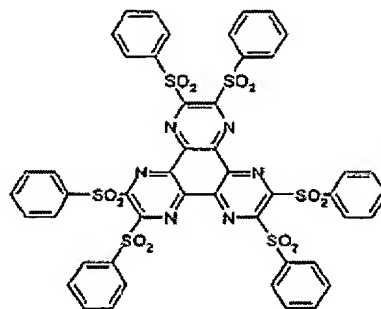
forming an insulating layer on the semi-conducting layer and the source and drain electrodes; and

forming a gate electrode in the insulating layer.

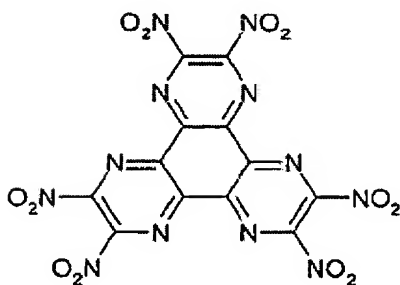
16. The method of claim 10, wherein the chemical compound I includes one of the following compounds Ia to Ig.



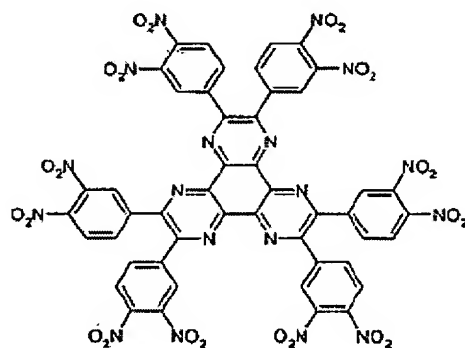
Formula Ia



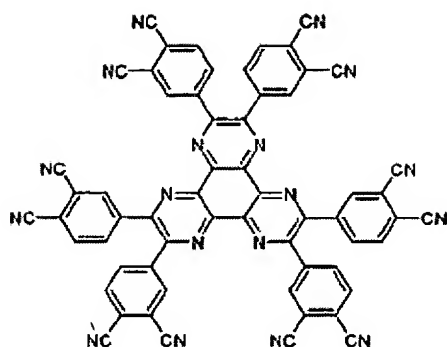
Formula Ib



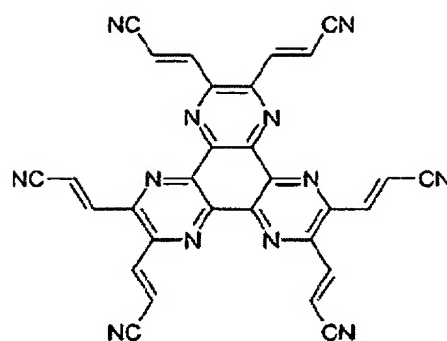
Formula Ic



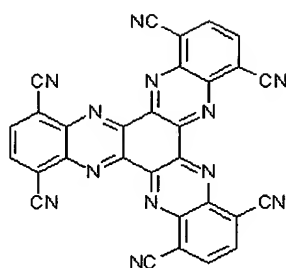
Formula Id



Formula 1e



Formula 1f



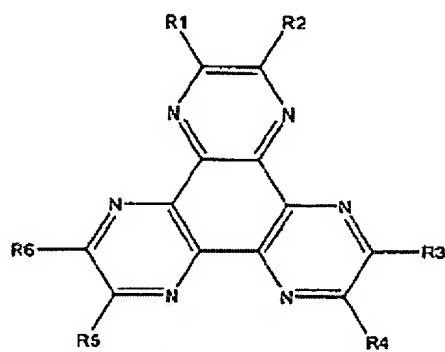
Formula 1g

17. The method of claim 10, further comprising forming the source and drain electrodes as one of aluminum, silver, gold, neodymium, palladium, platinum, gold, and alloys of the foregoing metals.

18. The method of claim 10, further comprising forming the source and drain electrodes with composite materials including aluminum or silver.

19. An organic transistor, comprising:

an organic layer including at least one compound represented by Chemical Formula I.



Formula I